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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I²C, IrDA, SmartCard, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	52
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-VFQFN Exposed Pad
Supplier Device Package	64-QFN (9x9)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32wg330f256-qfn64

1 Ordering Information

Table 1.1 (p. 2) shows the available EFM32WG330 devices.

Table 1.1. Ordering Information

Ordering Code	Flash (kB)	RAM (kB)	Max Speed (MHz)	Supply Voltage (V)	Temperature (°C)	Package
EFM32WG330F64-QFN64	64	32	48	1.98 - 3.8	-40 - 85	QFN64
EFM32WG330F128-QFN64	128	32	48	1.98 - 3.8	-40 - 85	QFN64
EFM32WG330F256-QFN64	256	32	48	1.98 - 3.8	-40 - 85	QFN64

Visit www.silabs.com for information on global distributors and representatives.

Module	Configuration	Pin Connections
I2C0	Full configuration	I2C0_SDA, I2C0_SCL
I2C1	Full configuration	I2C1_SDA, I2C1_SCL
USART0	Full configuration with IrDA	US0_TX, US0_RX, US0_CLK, US0_CS
USART1	Full configuration with I2S	US1_TX, US1_RX, US1_CLK, US1_CS
USART2	Full configuration with I2S	US2_TX, US2_RX, US2_CLK, US2_CS
LEUART0	Full configuration	LEU0_TX, LEU0_RX
LEUART1	Full configuration	LEU1_TX, LEU1_RX
TIMER0	Full configuration with DTI	TIM0_CC[2:0], TIM0_CDTI[2:0]
TIMER1	Full configuration	TIM1_CC[2:0]
TIMER2	Full configuration	TIM2_CC[2:0]
TIMER3	Full configuration	TIM3_CC[2:0]
RTC	Full configuration	NA
BURTC	Full configuration	NA
LETIMER0	Full configuration	LET0_O[1:0]
PCNT0	Full configuration, 16-bit count register	PCNT0_S[1:0]
PCNT1	Full configuration, 8-bit count register	PCNT1_S[1:0]
PCNT2	Full configuration, 8-bit count register	PCNT2_S[1:0]
ACMP0	Full configuration	ACMP0_CH[7:0], ACMP0_O
ACMP1	Full configuration	ACMP1_CH[7:0], ACMP1_O
VCMP	Full configuration	NA
ADC0	Full configuration	ADC0_CH[7:0]
DAC0	Full configuration	DAC0_OUT[1:0], DAC0_OUTxALT
OPAMP	Full configuration	Outputs: OPAMP_OUTx, OPAMP_OUTxALT, Inputs: OPAMP_Px, OPAMP_Nx
AES	Full configuration	NA
GPIO	52 pins	Available pins are shown in Table 4.3 (p. 61)

2.3 Memory Map

The EFM32WG330 memory map is shown in Figure 2.2 (p. 9), with RAM and Flash sizes for the largest memory configuration.

3 Electrical Characteristics

3.1 Test Conditions

3.1.1 Typical Values

The typical data are based on $T_{AMB}=25^{\circ}\text{C}$ and $V_{DD}=3.0\text{ V}$, as defined in Table 3.2 (p. 10), by simulation and/or technology characterisation unless otherwise specified.

3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 10), by simulation and/or technology characterisation unless otherwise specified.

3.2 Absolute Maximum Ratings

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 10) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 10).

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Condition	Min	Typ	Max	Unit
T_{STG}	Storage temperature range		-40		150 ¹	°C
T_S	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	°C
V_{DDMAX}	External main supply voltage		0		3.8	V
V_{IOPIN}	Voltage on any I/O pin		-0.3		$V_{DD}+0.3$	V

¹Based on programmed devices tested for 10000 hours at 150°C. Storage temperature affects retention of preprogrammed calibration values stored in flash. Please refer to the Flash section in the Electrical Characteristics for information on flash data retention for different temperatures.

3.3 General Operating Conditions

3.3.1 General Operating Conditions

Table 3.2. General Operating Conditions

Symbol	Parameter	Min	Typ	Max	Unit
T_{AMB}	Ambient temperature range	-40		85	°C
V_{DDOP}	Operating supply voltage	1.98		3.8	V
f_{APB}	Internal APB clock frequency			48	MHz
f_{AHB}	Internal AHB clock frequency			48	MHz

Figure 3.3. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 21MHz

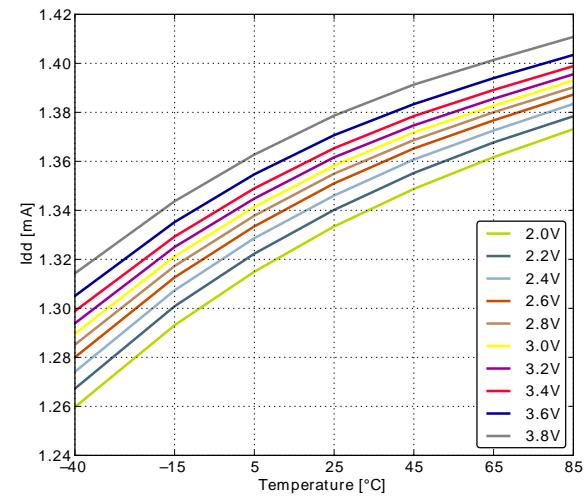
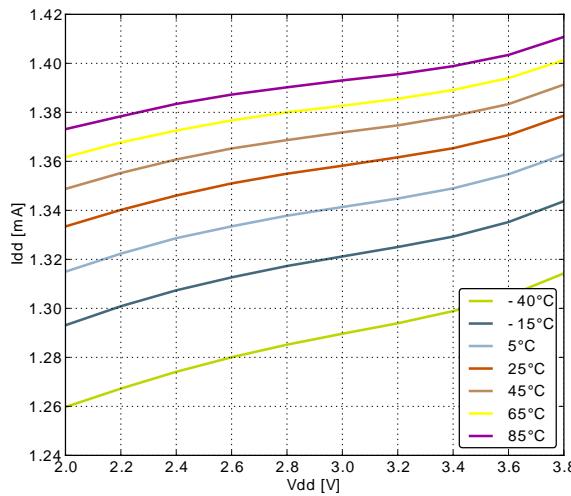
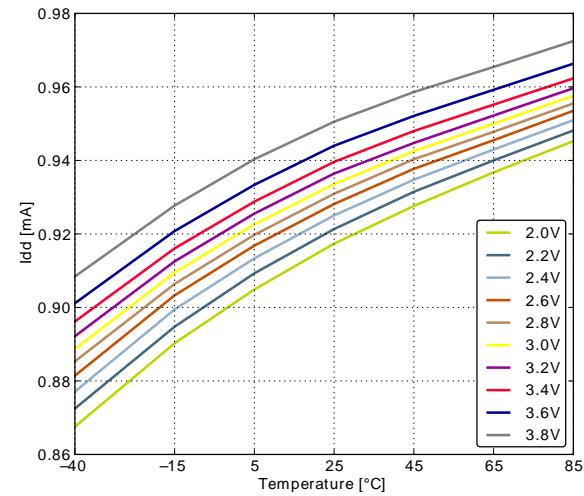
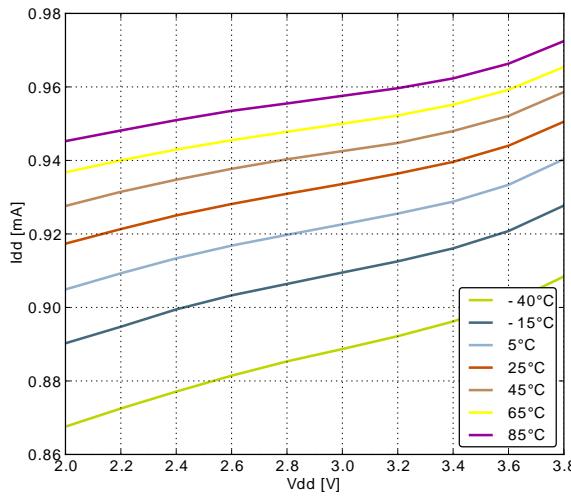
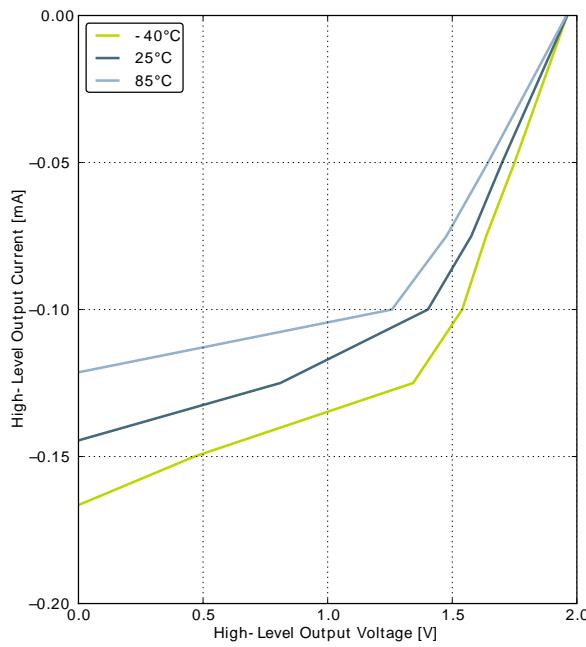


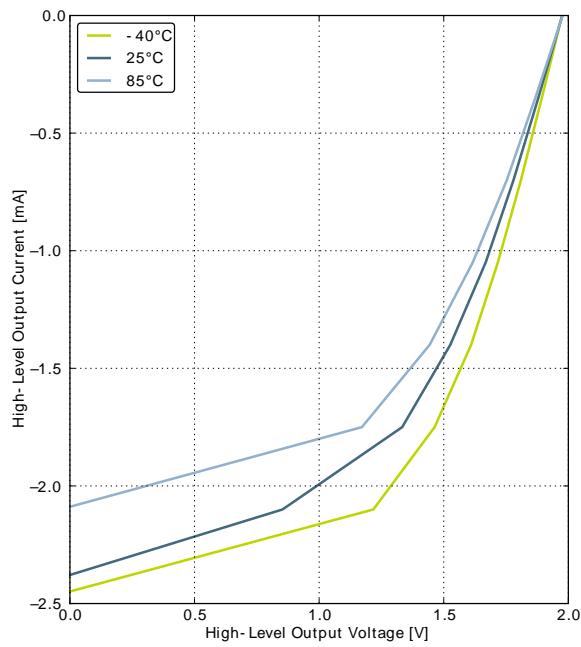
Figure 3.4. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 14MHz



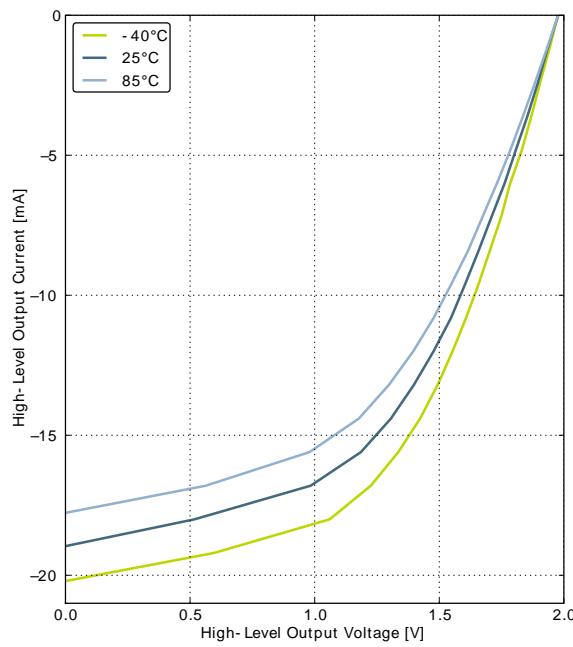
Symbol	Parameter	Condition	Min	Typ	Max	Unit
		Sourcing 20 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.80V _{DD}			V
V _{IOOL}	Output low voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sinking 0.1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.20V _{DD}		V
		Sinking 0.1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.10V _{DD}		V
		Sinking 1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.10V _{DD}		V
		Sinking 1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.05V _{DD}		V
		Sinking 6 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.30V _{DD}	V
		Sinking 6 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.20V _{DD}	V
		Sinking 20 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.35V _{DD}	V
		Sinking 20 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.25V _{DD}	V
I _{IOLEAK}	Input leakage current	High Impedance IO connected to GROUND or Vdd		±0.1	±100	nA
R _{PU}	I/O pin pull-up resistor			40		kOhm
R _{PD}	I/O pin pull-down resistor			40		kOhm
R _{IOESD}	Internal ESD series resistor			200		Ohm
t _{IOGLITCH}	Pulse width of pulses to be removed by the glitch suppression filter		10		50	ns
t _{IOOF}	Output fall time	GPIO_Px_CTRL DRIVEMODE = LOWEST and load capacitance C _L =12.5-25pF.	20+0.1C _L		250	ns
		GPIO_Px_CTRL DRIVEMODE = LOW and load capacitance C _L =350-600pF	20+0.1C _L		250	ns
V _{IOHYST}	I/O pin hysteresis (V _{IOTHR+} - V _{IOTHR-})	V _{DD} = 1.98 - 3.8 V	0.10V _{DD}			V

Figure 3.12. Typical High-Level Output Current, 2V Supply Voltage

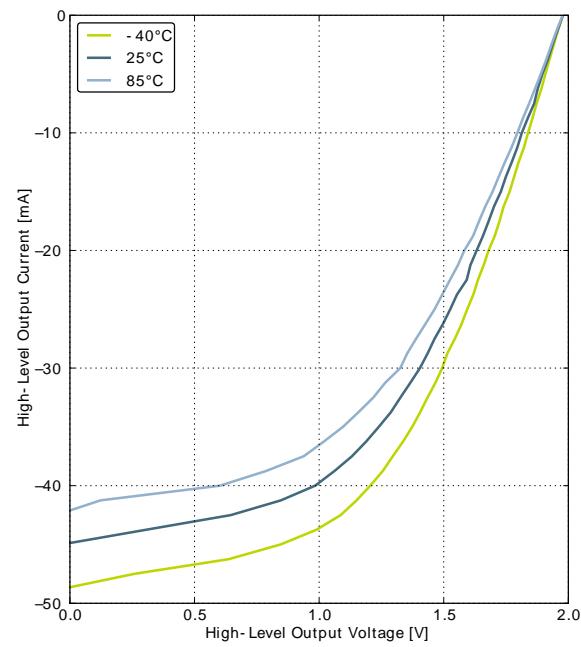
GPIO_Px_CTRL DRIVEMODE = LOWEST



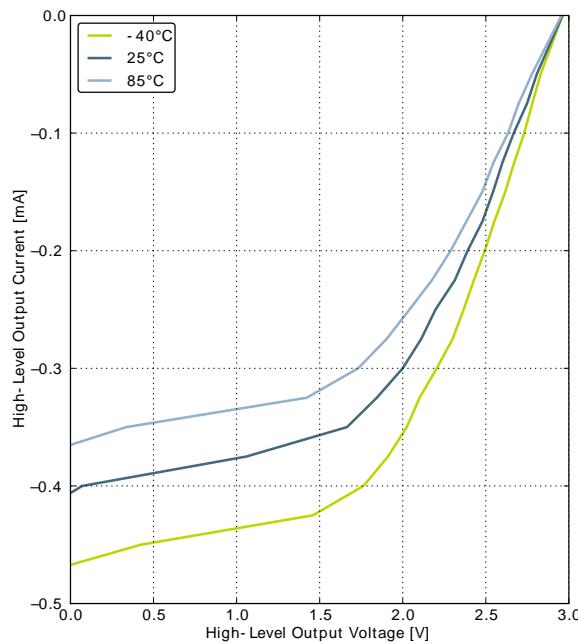
GPIO_Px_CTRL DRIVEMODE = LOW



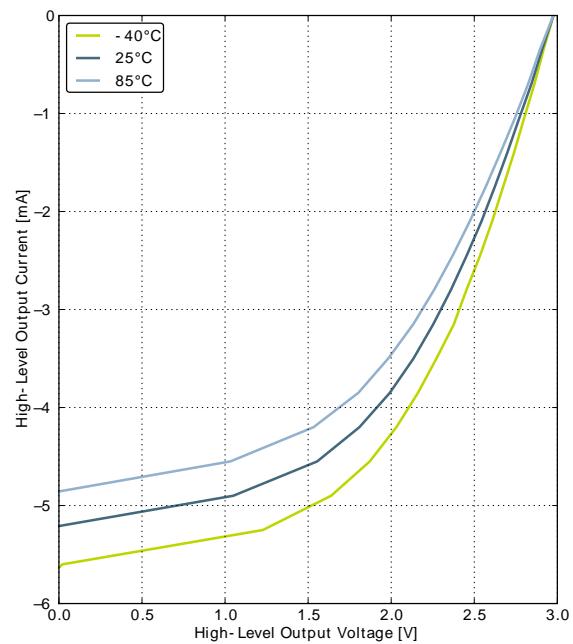
GPIO_Px_CTRL DRIVEMODE = STANDARD



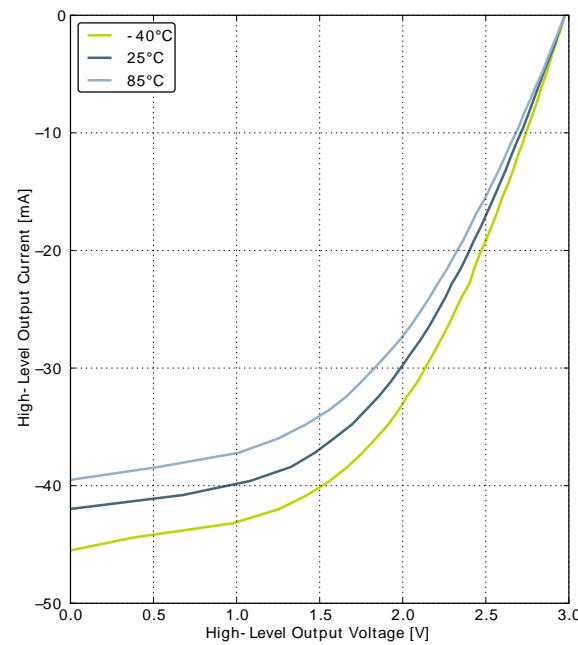
GPIO_Px_CTRL DRIVEMODE = HIGH

Figure 3.14. Typical High-Level Output Current, 3V Supply Voltage

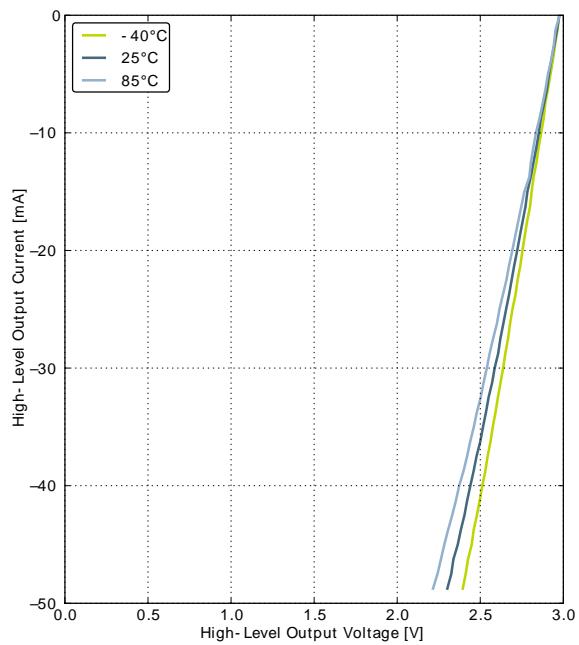
GPIO_Px_CTRL DRIVEMODE = LOWEST



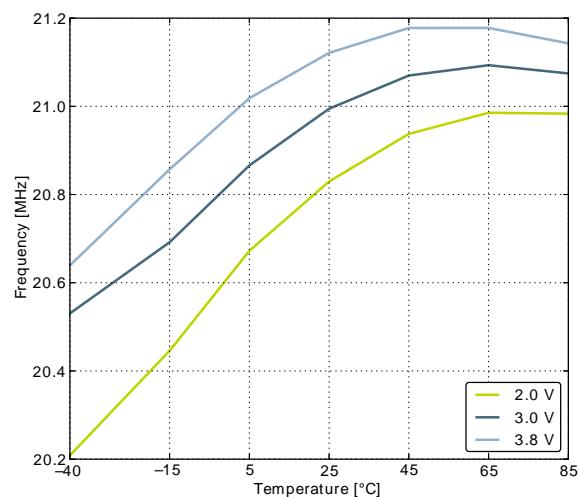
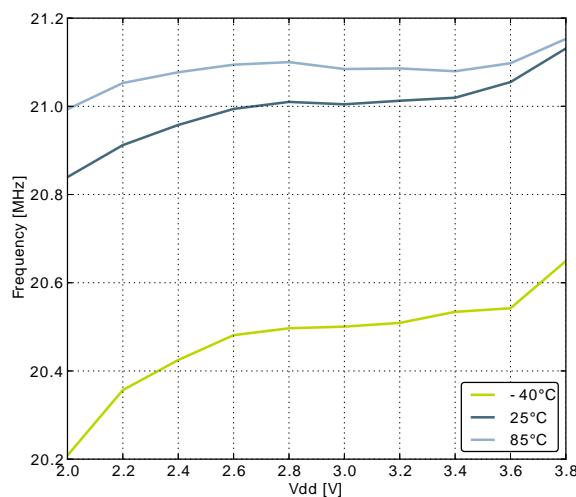
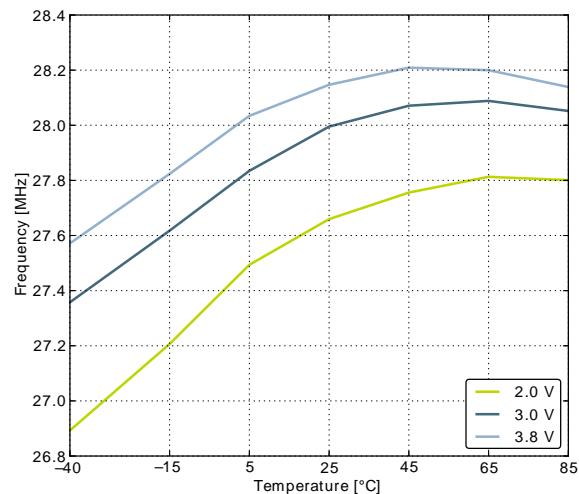
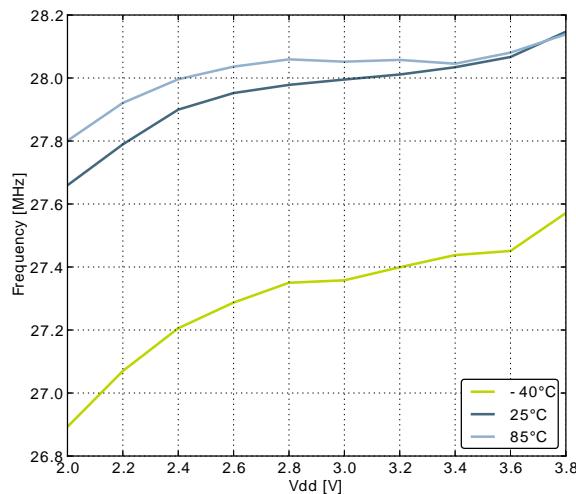
GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = HIGH

Figure 3.22. Calibrated HFRCO 21 MHz Band Frequency vs Supply Voltage and Temperature**Figure 3.23. Calibrated HFRCO 28 MHz Band Frequency vs Supply Voltage and Temperature**

3.9.5 AUXHFRCO

Table 3.13. AUXHFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$f_{AUXHFRCO}$	Oscillation frequency, $V_{DD} = 3.0\text{ V}$, $T_{AMB} = 25^\circ\text{C}$	28 MHz frequency band	27.5	28.0	28.5	MHz
		21 MHz frequency band	20.6	21.0	21.4	MHz
		14 MHz frequency band	13.7	14.0	14.3	MHz
		11 MHz frequency band	10.8	11.0	11.2	MHz
		7 MHz frequency band	6.48	6.60	6.72	MHz
		1 MHz frequency band	1.15	1.20	1.25	MHz
$t_{AUXHFRCO_settling}$	Settling time after start-up	$f_{AUXHFRCO} = 14\text{ MHz}$		0.6		Cycles
$DC_{AUXHFRCO}$	Duty cycle	$f_{AUXHFRCO} = 14\text{ MHz}$	48.5	50	51	%
$TUNESTEP_{AUXHFRCO}$	Frequency step for LSB change in TUNING value			0.3 ¹		%

¹The TUNING field in the CMU_AUXHFRCOCTRL register may be used to adjust the AUXHFRCO frequency. There is enough adjustment range to ensure that the frequency bands above 7 MHz will always have some overlap across supply voltage and temperature. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the AUXHFRCO frequency at any arbitrary value between 7 MHz and 28 MHz across operating conditions.

3.9.6 ULFRCO

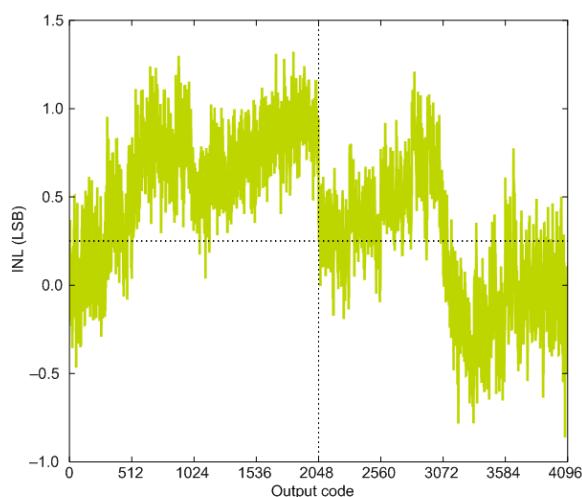
Table 3.14. ULFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{ULFRCO}	Oscillation frequency	25°C, 3V	0.7		1.75	kHz
TC_{ULFRCO}	Temperature coefficient			0.05		%/°C
VC_{ULFRCO}	Supply voltage coefficient			-18.2		%/V

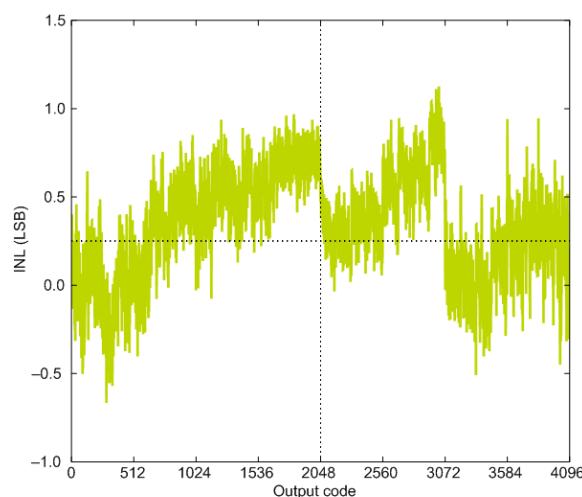
3.10 Analog Digital Converter (ADC)

Table 3.15. ADC

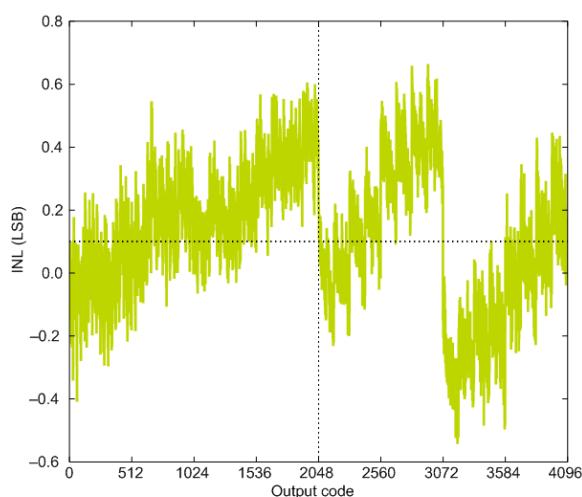
Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{ADCIN}	Input voltage range	Single ended	0		V_{REF}	V
		Differential	$-V_{REF}/2$		$V_{REF}/2$	V
$V_{ADCREFIN}$	Input range of external reference voltage, single ended and differential		1.25		V_{DD}	V
$V_{ADCREFIN_CH7}$	Input range of external negative reference voltage on channel 7	See $V_{ADCREFIN}$	0		$V_{DD} - 1.1$	V
$V_{ADCREFIN_CH6}$	Input range of external positive ref-	See $V_{ADCREFIN}$	0.625		V_{DD}	V

Figure 3.27. ADC Integral Linearity Error vs Code, Vdd = 3V, Temp = 25°C

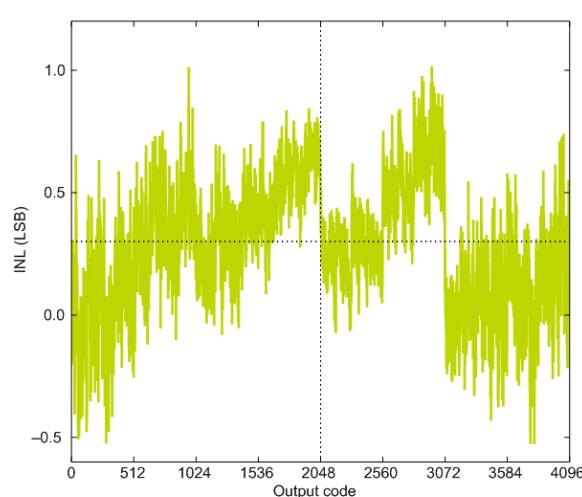
1.25V Reference



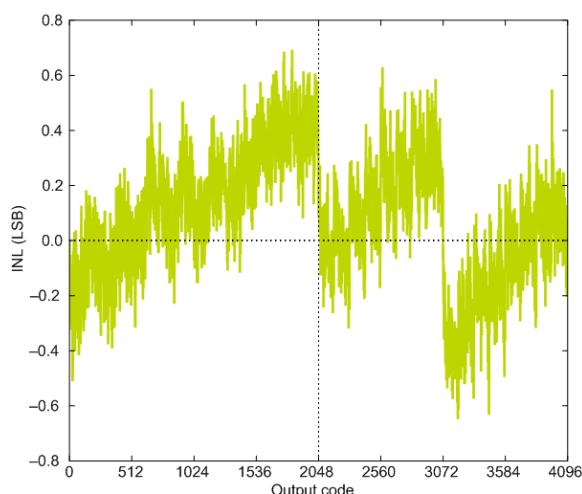
2.5V Reference



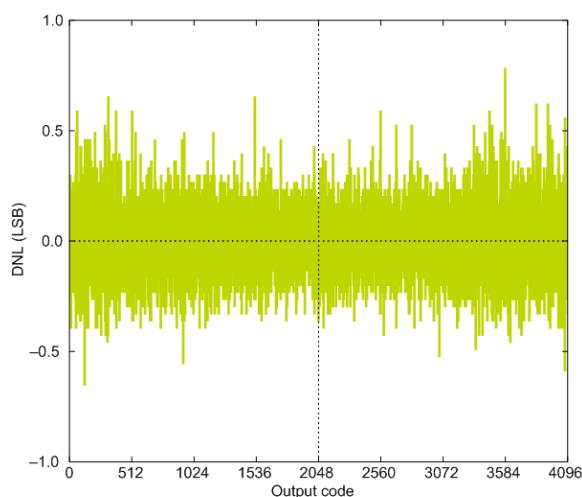
2XVDDVSS Reference



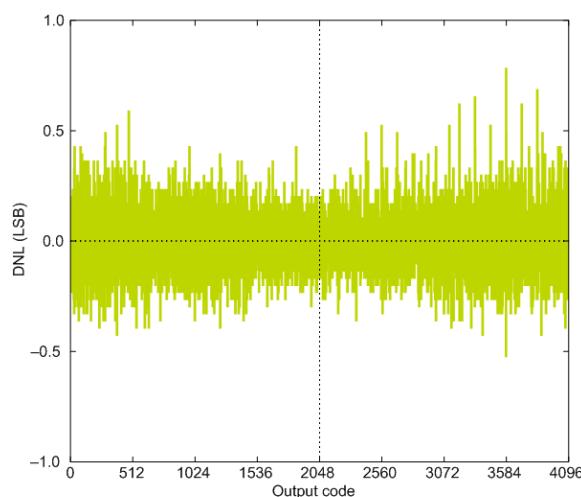
5VDIFF Reference



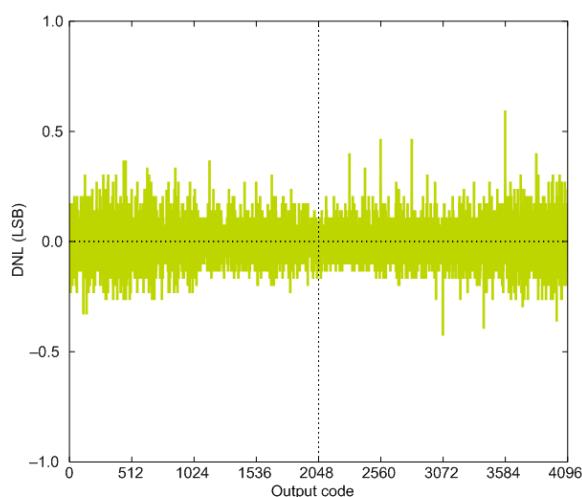
VDD Reference

Figure 3.28. ADC Differential Linearity Error vs Code, Vdd = 3V, Temp = 25°C

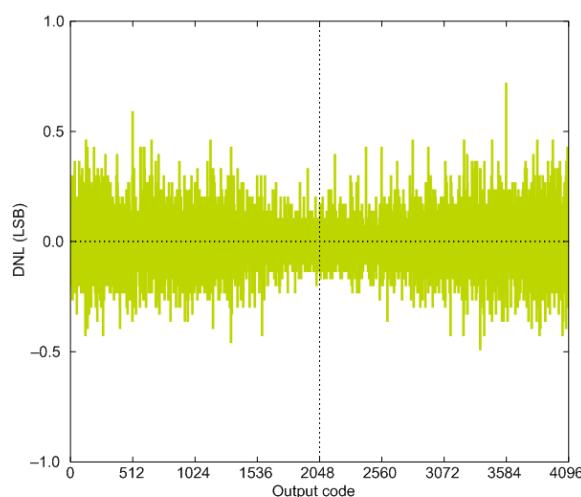
1.25V Reference



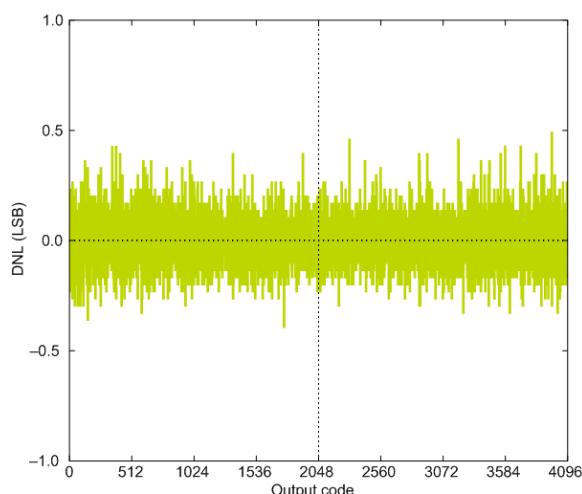
2.5V Reference



2XVDDVSS Reference



5VDIFF Reference



VDD Reference

Symbol	Parameter	Condition	Min	Typ	Max	Unit
SNDR_{DAC}	Signal to Noise-pulse Distortion Ratio (SNDR)	500 kSamples/s, 12 bit, differential, internal 2.5V reference		58		dB
		500 kSamples/s, 12 bit, differential, V_{DD} reference		59		dB
		500 kSamples/s, 12 bit, single ended, internal 1.25V reference		57		dB
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		54		dB
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		56		dB
	Spurious-Free Dynamic Range(SFDR)	500 kSamples/s, 12 bit, differential, internal 2.5V reference		53		dB
		500 kSamples/s, 12 bit, differential, V_{DD} reference		55		dB
		500 kSamples/s, 12 bit, single ended, internal 1.25V reference		62		dBc
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		56		dBc
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		61		dBc
SFDR_{DAC}	Offset voltage	500 kSamples/s, 12 bit, differential, internal 2.5V reference		55		dBc
		500 kSamples/s, 12 bit, differential, V_{DD} reference		60		dBc
		After calibration, single ended		2	9	mV
		After calibration, differential		2		mV
DNL_{DAC}	Differential non-linearity			± 1		LSB
INL_{DAC}	Integral non-linearity			± 5		LSB
MC_{DAC}	No missing codes			12		bits

¹Measured with a static input code and no loading on the output.

3.12 Operational Amplifier (OPAMP)

The electrical characteristics for the Operational Amplifiers are based on simulations.

Table 3.17. OPAMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{OPAMP}	Active Current	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0, Unity Gain		370	460	μA
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1, Unity Gain		95	135	μA

3.14 Voltage Comparator (VCMP)

Table 3.19. VCMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{VCMPIN}	Input voltage range			V _{DD}		V
V _{VCMPCM}	VCMP Common Mode voltage range			V _{DD}		V
I _{VCMP}	Active current	BIASPROG=0b0000 and HALFBIAS=1 in VCMPn_CTRL register		0.3	0.6	µA
		BIASPROG=0b1111 and HALFBIAS=0 in VCMPn_CTRL register. LPREF=0.		22	35	µA
t _{VCMPREF}	Startup time reference generator	NORMAL		10		µs
V _{VCMPOFFSET}	Offset voltage	Single ended		10		mV
		Differential		10		mV
V _{VCMPHYST}	VCMP hysteresis			61	210	mV
t _{VCMPSTART}	Startup time				10	µs

The V_{DD} trigger level can be configured by setting the TRIGLEVEL field of the VCMP_CTRL register in accordance with the following equation:

VCMP Trigger Level as a Function of Level Setting

$$V_{DD \text{ Trigger Level}} = 1.667V + 0.034 \times \text{TRIGLEVEL} \quad (3.2)$$

3.15 I2C

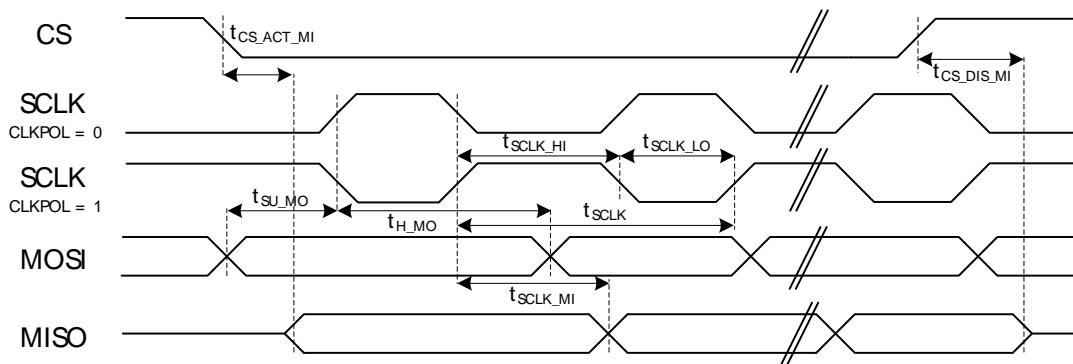
Table 3.20. I2C Standard-mode (Sm)

Symbol	Parameter	Min	Typ	Max	Unit
f _{SCL}	SCL clock frequency	0		100 ¹	kHz
t _{LOW}	SCL clock low time	4.7			µs
t _{HIGH}	SCL clock high time	4.0			µs
t _{SU,DAT}	SDA set-up time	250			ns
t _{HD,DAT}	SDA hold time	8		3450 ^{2,3}	ns
t _{SU,STA}	Repeated START condition set-up time	4.7			µs
t _{HD,STA}	(Repeated) START condition hold time	4.0			µs
t _{SU,STO}	STOP condition set-up time	4.0			µs
t _{BUF}	Bus free time between a STOP and a START condition	4.7			µs

¹For the minimum HFPERCLK frequency required in Standard-mode, see the I2C chapter in the EFM32WG Reference Manual.

²The maximum SDA hold time (t_{HD,DAT}) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).

³When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < ((3450*10⁻⁹ [s] * f_{HFPERCLK} [Hz]) - 4).

Figure 3.39. SPI Slave Timing**Table 3.25. SPI Slave Timing**

Symbol	Parameter	Min	Typ	Max	Unit
$t_{SCLK_sl}^{1,2}$	SCLK period	$6 * t_{HFPER-CLK}$			ns
$t_{SCLK_hi}^{1,2}$	SCLK high period	$3 * t_{HFPER-CLK}$			ns
$t_{SCLK_lo}^{1,2}$	SCLK low period	$3 * t_{HFPER-CLK}$			ns
$t_{CS_ACT_MI}^{1,2}$	CS active to MISO	5.00		35.00	ns
$t_{CS_DIS_MI}^{1,2}$	CS disable to MISO	5.00		35.00	ns
$t_{SU_MO}^{1,2}$	MOSI setup time	5.00			ns
$t_{H_MO}^{1,2}$	MOSI hold time	$2 + 2 * t_{HFPERCLK}$			ns
$t_{SCLK_MI}^{1,2}$	SCLK to MISO	$7 + t_{HFPER-CLK}$		$42 + 2 * t_{HFPERCLK}$	ns

¹ Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)

² Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

Table 3.26. SPI Slave Timing with SSSEARLY and SMSDELAY

Symbol	Parameter	Min	Typ	Max	Unit
$t_{SCLK_sl}^{1,2}$	SCLK period	$6 * t_{HFPER-CLK}$			ns
$t_{SCLK_hi}^{1,2}$	SCLK high period	$3 * t_{HFPER-CLK}$			ns
$t_{SCLK_lo}^{1,2}$	SCLK low period	$3 * t_{HFPER-CLK}$			ns
$t_{CS_ACT_MI}^{1,2}$	CS active to MISO	5.00		35.00	ns
$t_{CS_DIS_MI}^{1,2}$	CS disable to MISO	5.00		35.00	ns
$t_{SU_MO}^{1,2}$	MOSI setup time	5.00			ns
$t_{H_MO}^{1,2}$	MOSI hold time	$2 + 2 * t_{HFPERCLK}$			ns

Symbol	Parameter	Min	Typ	Max	Unit
t_{SCLK_MI} ¹²	SCLK to MISO	-264 + $t_{HF\text{-}PERCLK}$		-234 + 2 * $t_{HF\text{PERCLK}}$	ns

¹ Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)

² Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

3.17 Digital Peripherals

Table 3.27. Digital Peripherals

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I _{USART}	USART current	USART idle current, clock enabled		4.0		µA/MHz
I _{UART}	UART current	UART idle current, clock enabled		3.8		µA/MHz
I _{LEUART}	LEUART current	LEUART idle current, clock enabled		194.0		nA
I _{I2C}	I2C current	I2C idle current, clock enabled		7.6		µA/MHz
I _{TIMER}	TIMER current	TIMER_0 idle current, clock enabled		6.5		µA/MHz
I _{LETIMER}	LETIMER current	LETIMER idle current, clock enabled		85.8		nA
I _{PCNT}	PCNT current	PCNT idle current, clock enabled		91.4		nA
I _{RTC}	RTC current	RTC idle current, clock enabled		54.6		nA
I _{AES}	AES current	AES idle current, clock enabled		1.8		µA/MHz
I _{GPIO}	GPIO current	GPIO idle current, clock enabled		3.4		µA/MHz
I _{PRS}	PRS current	PRS idle current		3.9		µA/MHz
I _{DMA}	DMA current	Clock enable		10.9		µA/MHz

QFN64 Pin# and Name		Pin Alternate Functionality / Description				
Pin #	Pin Name	Analog	Timers		Communication	Other
57	PE9		PCNT2_S1IN #1			
58	PE10		TIM1_CC0 #1		US0_TX #0	BOOT_TX
59	PE11		TIM1_CC1 #1		US0_RX #0	LES_ALTEX5 #0 BOOT_RX
60	PE12		TIM1_CC2 #1		US0_RX #3 US0_CLK #0 I2C0_SDA #6	CMU_CLK1 #2 LES_ALTEX6 #0
61	PE13				US0_TX #3 US0_CS #0 I2C0_SCL #6	LES_ALTEX7 #0 ACMP0_O #0 GPIO_EM4WU5
62	PE14		TIM3_CC0 #0		LEU0_TX #2	
63	PE15		TIM3_CC1 #0		LEU0_RX #2	
64	PA15		TIM3_CC2 #0			

4.2 Alternate Functionality Pinout

A wide selection of alternate functionality is available for multiplexing to various pins. This is shown in Table 4.2 (p. 57). The table shows the name of the alternate functionality in the first column, followed by columns showing the possible LOCATION bitfield settings.

Note

Some functionality, such as analog interfaces, do not have alternate settings or a LOCATION bitfield. In these cases, the pinout is shown in the column corresponding to LOCATION 0.

Table 4.2. Alternate functionality overview

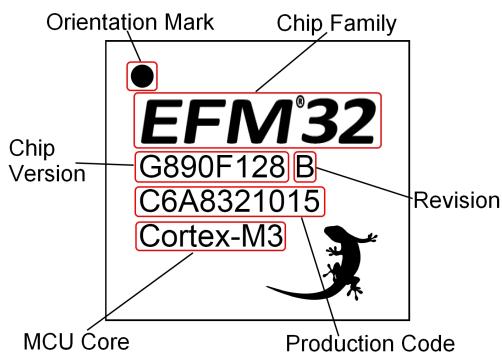
Alternate	LOCATION							
Functionality	0	1	2	3	4	5	6	Description
ACMP0_CH0	PC0							Analog comparator ACMP0, channel 0.
ACMP0_CH1	PC1							Analog comparator ACMP0, channel 1.
ACMP0_CH2	PC2							Analog comparator ACMP0, channel 2.
ACMP0_CH3	PC3							Analog comparator ACMP0, channel 3.
ACMP0_CH4	PC4							Analog comparator ACMP0, channel 4.
ACMP0_CH5	PC5							Analog comparator ACMP0, channel 5.
ACMP0_CH6	PC6							Analog comparator ACMP0, channel 6.
ACMP0_CH7	PC7							Analog comparator ACMP0, channel 7.
ACMP0_O	PE13		PD6					Analog comparator ACMP0, digital output.
ACMP1_CH0	PC8							Analog comparator ACMP1, channel 0.
ACMP1_CH1	PC9							Analog comparator ACMP1, channel 1.
ACMP1_CH2	PC10							Analog comparator ACMP1, channel 2.
ACMP1_CH3	PC11							Analog comparator ACMP1, channel 3.
ACMP1_O	PF2		PD7					Analog comparator ACMP1, digital output.
ADC0_CH0	PD0							Analog to digital converter ADC0, input channel number 0.
ADC0_CH1	PD1							Analog to digital converter ADC0, input channel number 1.

6 Chip Marking, Revision and Errata

6.1 Chip Marking

In the illustration below package fields and position are shown.

Figure 6.1. Example Chip Marking (top view)



6.2 Revision

The revision of a chip can be determined from the "Revision" field in Figure 6.1 (p. 67) .

6.3 Errata

Please see the errata document for EFM32WG330 for description and resolution of device erratas. This document is available in Simplicity Studio and online at:

<http://www.silabs.com/support/pages/document-library.aspx?p=MCUs--32-bit>

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